

IFW

TRANSMITTAL OF FORMAL DRAWINGS

Docket No.
FIS920030412US1

In Re Application Of: Khater, et al.

Serial No.

Filing Date

Confirmation No.

Examiner

Art Unit

10/709,220

4/22/04

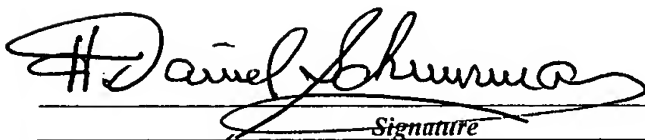
Invention: Structure and Method of Forming Bipolar Transistor Having a Self-Aligned Raised Extrinsic Base Using Self Aligned Etch Stop Layer

Address to:
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Transmitted herewith are:

12 sheets of formal drawing(s) for this application.

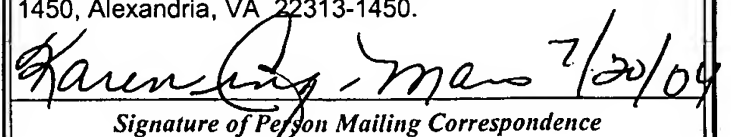
☒ Each sheet of drawing indicates the identifying indicia suggested in 37 CFR Section 1.84(c).


Signature

H. Daniel Schnurmann
Agent
REGISTRATION NO.: 35,791

Dated: July 20, 2004

I certify that this document and attached formal drawings are being deposited on July 20, 2004 with the U.S. Postal Service as first class mail under 37 C.F.R. 1.8 and addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.


Signature of Person Mailing Correspondence

KAREN CINQ-MARS

Typed or Printed Name of Person Mailing Correspondence